

EUV Light Source Development at Energetiq

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Electrodeless
Z-Pinch™ Plasma

Energetiq's EUV light sources are the industry standard source for EUV infrastructure R&D, inspection, resist development, outgassing, mirror testing, and more.

The Electrodeless Z-Pinch™ EUV Source is a reliable and stable source of EUV photons and is being operated in the field 24/7 with consistent operation over many years.

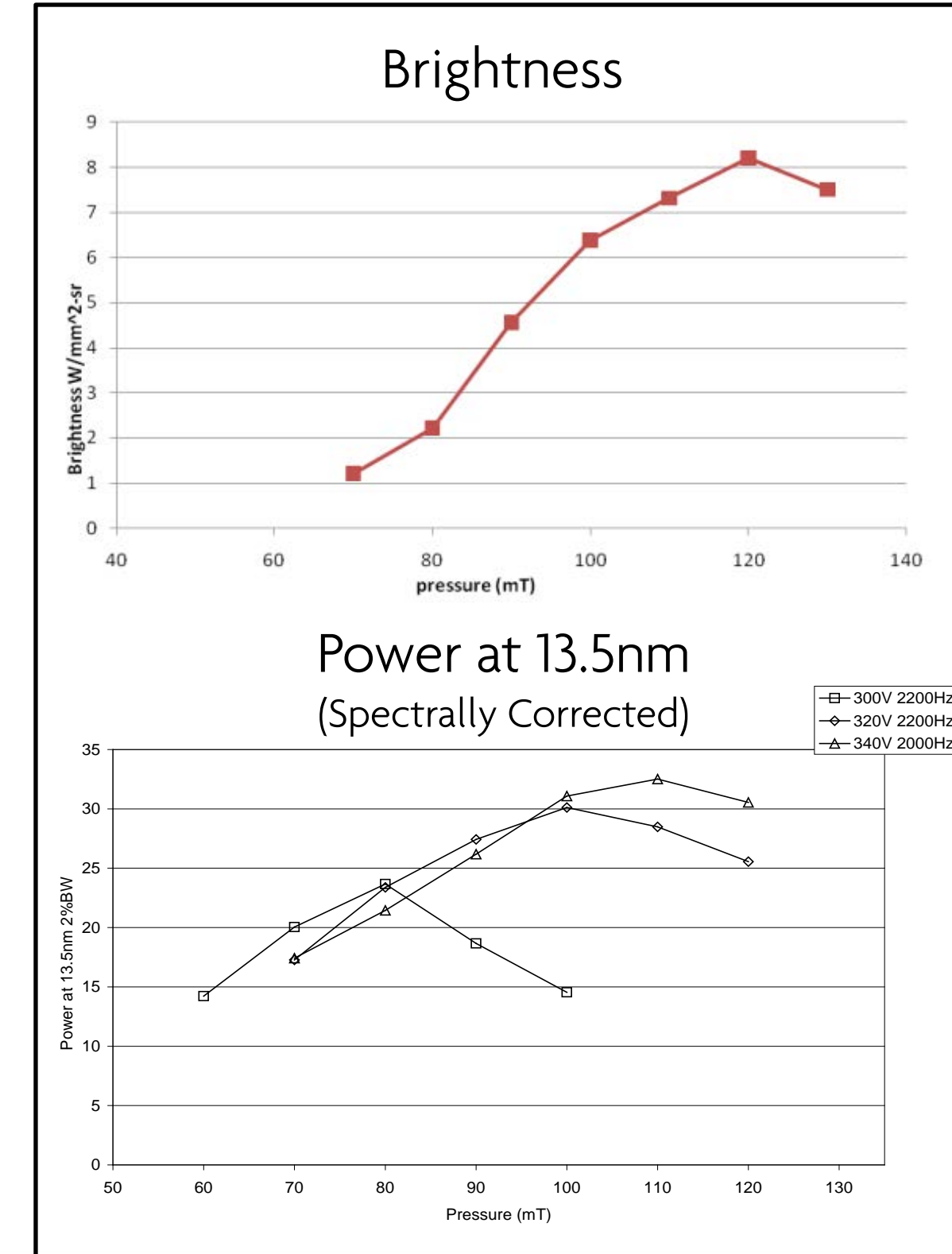
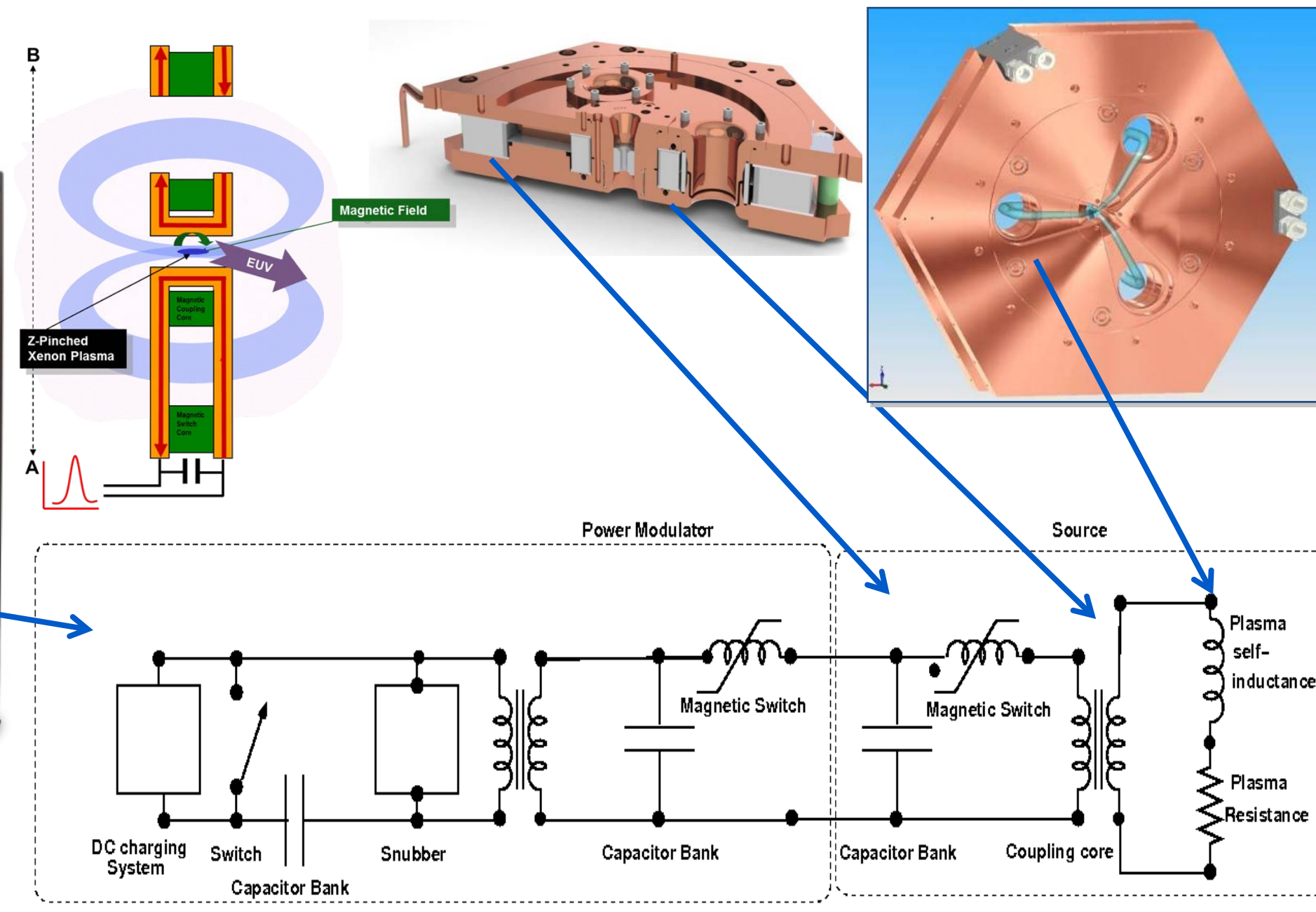
Key Features:

- 20 W of 13.5nm $\pm 1\%$ Power in 2π
- ~ 8 W/mm²-sr brightness
- >95% uptime; 24/7 stable operation
- Low cost of ownership

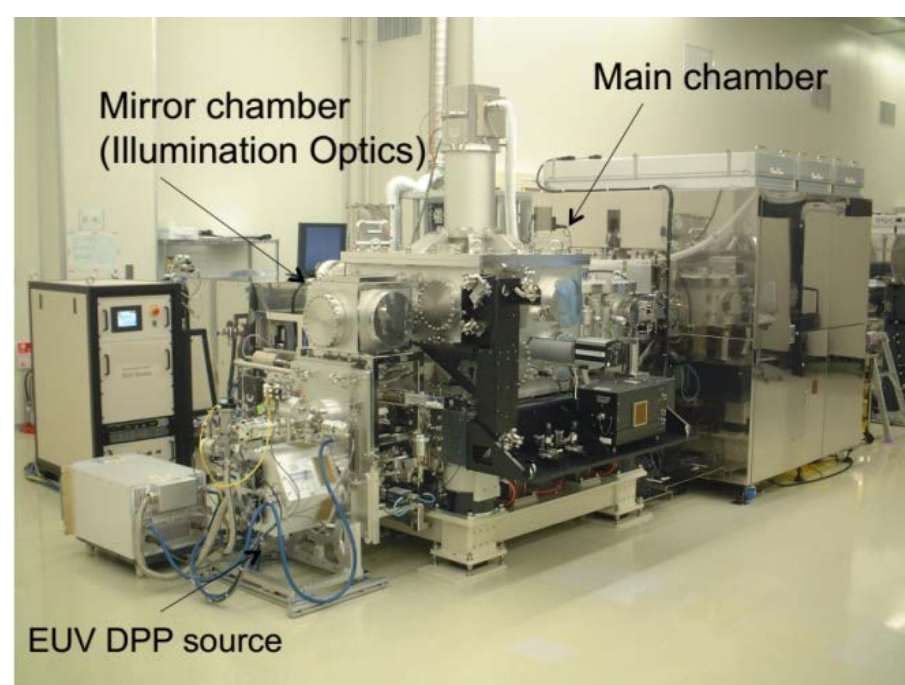
Patented Electrodeless Z-Pinch™



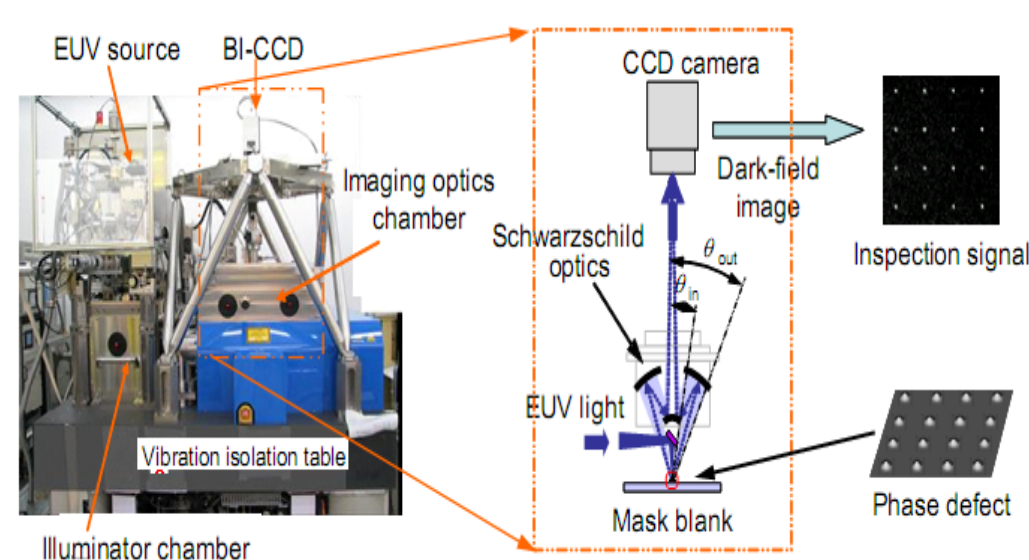
Inductively driven,
Electrodeless Z-Pinch™ –
integrated magnetic switch.



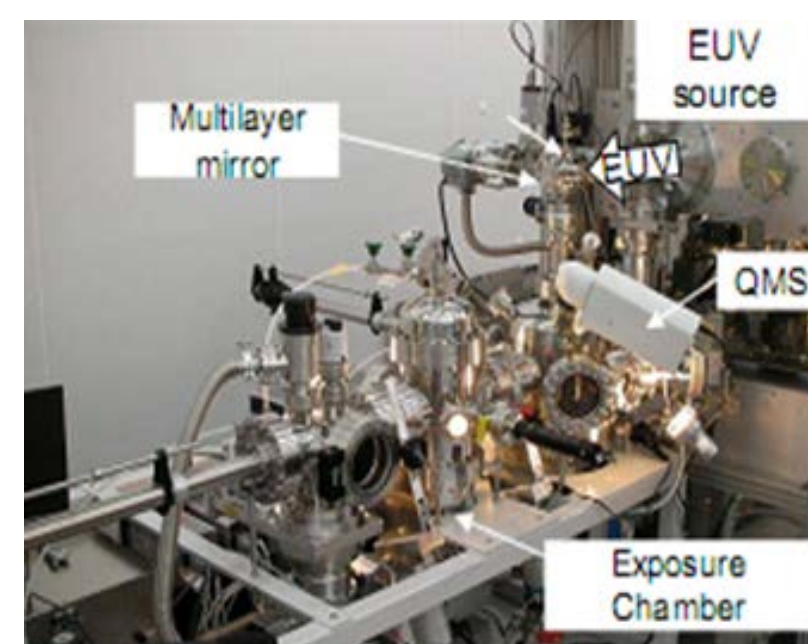
Applications and Installations (>30 units delivered)



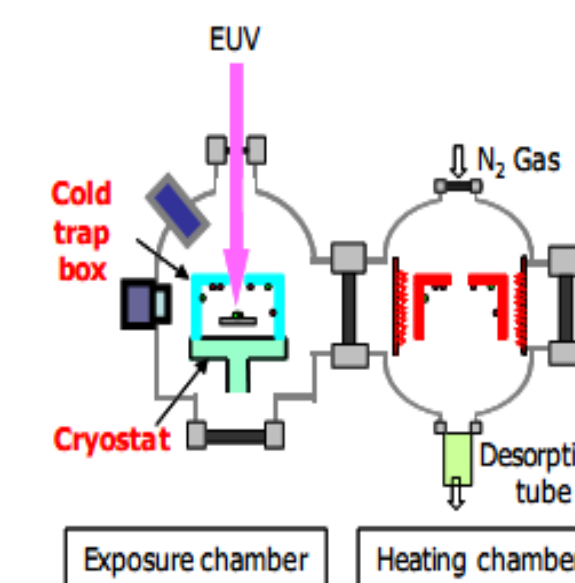
Lasertec/EIDEC mask inspection
tool [2, 3]



Actinic mask inspection tool at
Selete [4]



EUV technology outgassing tool at IMEC [6]



Flood exposure system at Osaka
University [5]



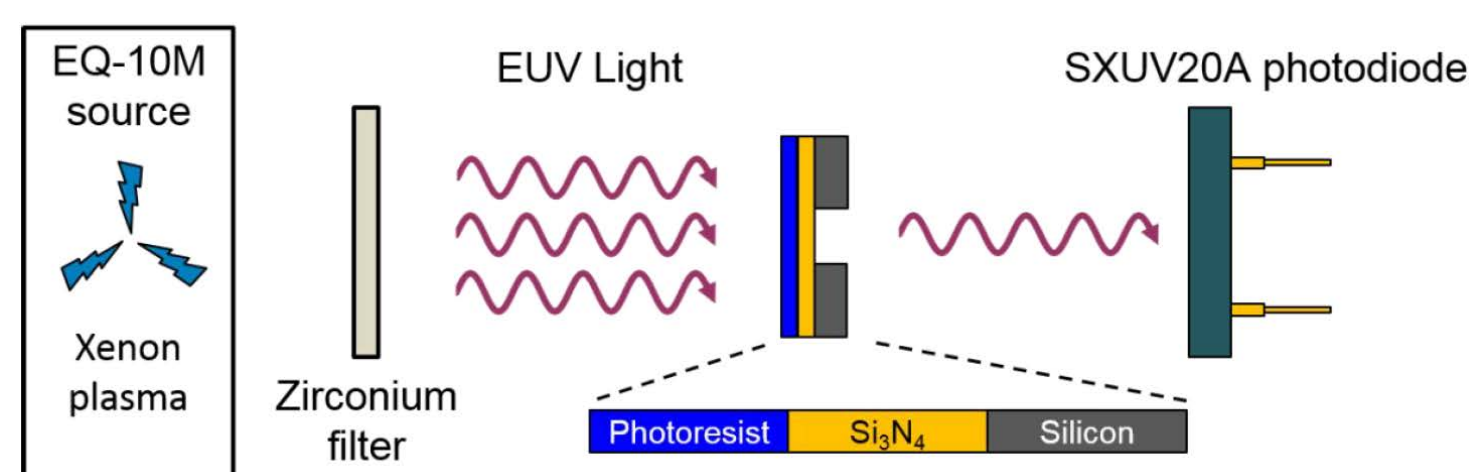
LithoTech outgassing tool at Selete [7]



shipped



Actinic mask inspection with AIMS™ [8]



Resist reactivity at SUNY Poly at Albany [9]

References

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